

# Design of High Efficiency Flyback Converter with Energy Regenerative Snubber

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**Abstract-**The Flyback converter is frequently used for multiple outputs and low power application due to its simplicity and both step-up and step-down characteristics. However, the high leakage inductance of the flyback transformer can causes high voltage spike and could damage the main transistor when the switch is turned off. Therefore, a turn-off snubber is needed to limit the peak voltage stress. In this paper, some common snubbers are discussed in comparison with the energy regenerative snubber. The operation of the energy regenerative snubber is analyzed and the design procedures are optimized for energy efficiency followed by experimental verification.

## I. INTRODUCTION

Low component count has been a notable advantage of the Flyback. In this converter, only one magnetic component is required to perform both the isolation and filter functions. One challenge in design the Flyback converter is handling the high leakage inductance of flyback transformer that causes high voltage spike and could damage the main transistor when it is turned off. A variety of turn-off snubbers were reported to limit the rate of rise voltage across the switching device, such as the conventional dissipative RCD snubbers and some non-dissipative snubbers. The RCD snubber is simple, but the power stored in snubber capacitor dissipates on the resistor, thus the efficiency suffers. The LC snubber proposed in [1] achieves lossless operation, but requires an additional inductor that increases the component cost. The energy regenerative snubber developed at UCI Power Electronics Labortory [4] uses the same number of component as RCD yet allows the clamp voltage to be much lower. It can recover leakage energy from snubber capacitor to the dc bus, thus improving energy efficiency.

In Fig.1 (a) a RCD snubber is in parallel with the primary winding. The power stored in the capacitor during turn off period is dissipated on the resistor when switch is turned on. As a result the power loss of dissipative snubbers is significant that cannot meet high efficiency requirement for modern power supply. Fig. 1 (b) shows a non-dissipative LC snubber. It uses combination of diode, inductor and capacitor to transport and store energy without dissipating it. The turn off switching loss can obviously be decreased. Article [3] proposed energy regenerative snubber that has low component count in addition to the advantage of the non-dissipative LC

snubber. In this paper, design and optimization of energy regenerative snubber was performed. Engineering design guidelines are provided. An experimental prototype was built to verify the theoretical findings.

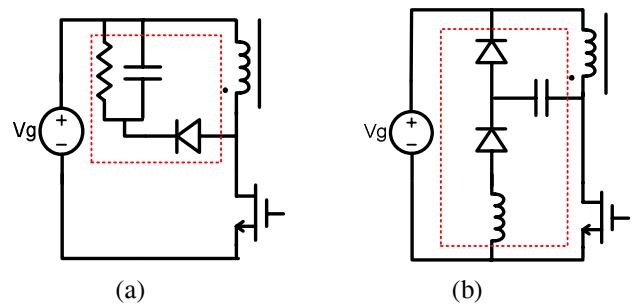


Fig 1. (a) Dissipative RCD snubber  
 (b) Non-dissipative LC snubber

## II. ANAYYSIS OF ENERGY REGENERATIVE SNUBBER

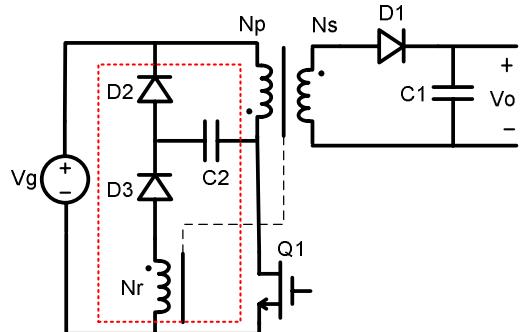


Fig. 2. Flyback with energy regenerative snubber

Table I Devices conduction modes

	$t_0 \sim t_1$	$t_1 \sim t_2$	$t_2 \sim t_3$	$t_3 \sim t_4$
MOSFET	ON	OFF	OFF	OFF
Diode 1	OFF	OFF	ON	ON
Diode 2	OFF	OFF	ON	OFF
Diode 3	ON	OFF	OFF	OFF

Fig. 2. shows a flyback converter with energy regenerative snubber. Although only one output is studied, the energy saving principle is applicable to multiple windings. This

converter has four switching operating modes as highlighted in Table I. Note that the transformer has three windings with turns ratio  $N_p$ :  $N_s$  and magnetizing inductance  $L_m$  is large compared with the leakage inductance  $L_{LK}$ .

In interval t0~t1: When  $Q_1$  is turned on,  $D_3$  conducts and  $C_2$  discharges through  $Q_1$  and reset winding  $N_r$ .  $V_g$  is applied on  $L_m$  and  $L_{LK}$ . The equivalent circuit during this interval is shown in Fig.3. (b)

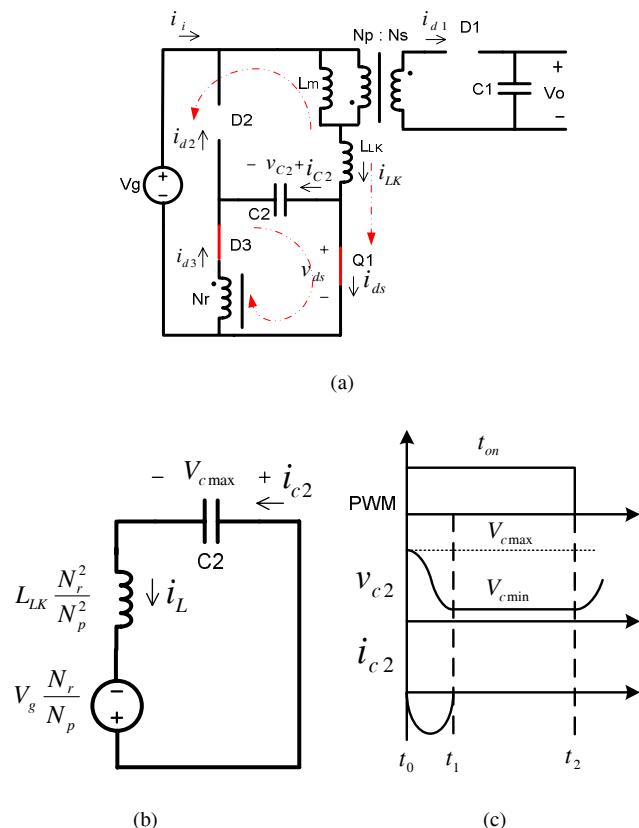


Fig. 3. (a) Interval t0~t1 sub-circuit  
 (b) Equivalent circuit of interval t0~t1  
 (c) Voltage and current waveforms of  $C_2$

From the equivalent circuit, the capacitor voltage and inductor current of this resonant circuit can be expressed as

$$v_{c2}(t) = V_g \frac{N_r}{N_p} - (V_g \frac{N_r}{N_p} - V_{c\max}) \cos \omega_0 t \quad (1)$$

$$i_L(t) = \frac{(V_g \frac{N_r}{N_p} - V_{c\max})}{Z_0} \sin \omega_0 t \quad (2)$$

Where angular resonance frequency is

$$\omega_0 = \frac{1}{N_p \sqrt{L_{LK} C_2}} \quad (3)$$

Characteristic impedance is

$$Z_o = \frac{N_r}{N_p} \sqrt{\frac{L_{LK}}{C_2}} \quad (4)$$

It is easy to see from Fig.3. (c) that  $V_{c\min}$  occurs at half resonant cycle  $\omega_0 t = \pi$ . Substitute this condition to (1) results following equation.

$$V_{c\min} = 2V_g \frac{N_r}{N_p} - V_{c\max} \quad (5)$$

In interval t1~t2: After t1,  $D_3$  ceases conducting once  $i_{c2}$  flows toward reverse direction.  $L_m$  is charged by dc bus and the voltage of  $C_2$  remains to be  $V_{c\min}$  until  $Q_1$  is turned off.

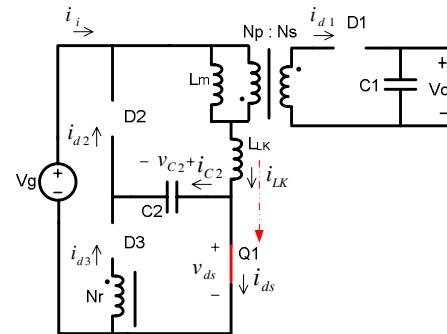


Fig. 4. Interval t1~t2 sub-circuit

In interval t2~t3:  $Q_1$  is turned off and  $D_2$  conducts. The energy stored in  $L_{LK}$  transfers to  $C_2$  and the peak voltage stress of switch is limited by the clamp voltage of  $C_2$ . Equations during  $t2 \sim t3$  for this resonant circuit is

$$i_L(t) = i_L \cos \omega_0 t + \frac{V_o \frac{N_p}{N_s} - V_{c\min}}{Z_0} \sin \omega_0 t \quad (6)$$

$$v_c(t) = V_o \frac{N_p}{N_s} - (V_o \frac{N_p}{N_s} - V_{c\min}) \cos \omega_0 t + Z_0 \cdot i_L \sin \omega_0 t \quad (7)$$

Where  $i_{Lm}$  in (7) is the magnetizing current  $I_m$ . The capacitance of  $C_2$  should be selected to have  $V_{c\min}$  equal  $V_o * N_p / N_s$ . Substitute those quantities into (6) and (7) yields following relationships.

$$i_L(t) = I_m \cos \omega_0 t \quad (8)$$

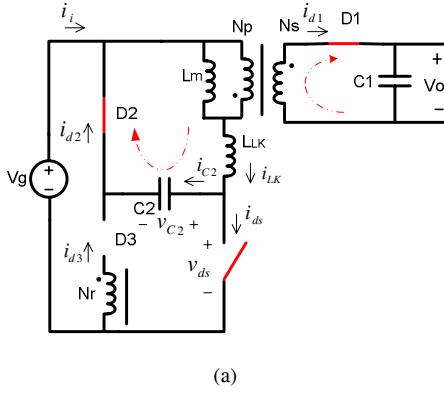
$$v_c(t) = V_o \frac{N_p}{N_s} + Z_0 \cdot I_m \sin \omega_0 t \quad (9)$$

From (8), the current in leakage inductance drops to zero at  $\pi/2$ . At this moment,  $v_c(t)$  reaches the maximum clamp voltage  $V_{c\max}$ .

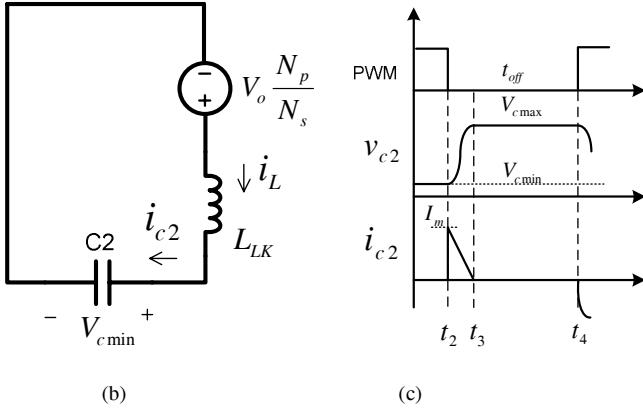
$$V_{c\max} = V_o \frac{N_p}{N_s} + Z_0 \cdot I_m = V_{c\min} + I_m \cdot \sqrt{\frac{L_{LK}}{C_2}} \quad (10)$$

Substitution of (5) and (10) yields

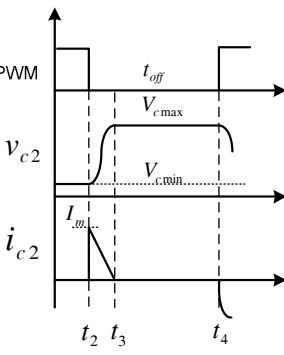
$$V_{c\min} = V_g \frac{N_r}{N_p} - \frac{I_m}{2} \sqrt{\frac{L_{LK}}{C_2}} \quad (11)$$



(a)



(b)



(c)

Fig. 5. (a) Interval t2~t3 sub-circuit

(b) Equivalent circuit of interval t2~t3

(c) Voltage and current waveforms of C2

In interval t3~t4: After t3, the current in the leakage inductance decreases to zero until the next turn-on state. The whole processes of four intervals repeat in each cycle. The analysis shows that the snubber capacitor C<sub>2</sub> and reset winding N<sub>r</sub> are two crucial parameters to the operation of circuit. The design procedures will be depicted in the next section.

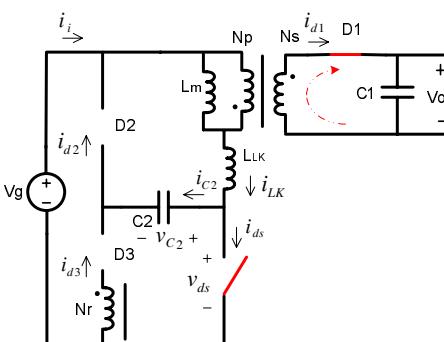


Fig. 6. Interval t3~t4 sub-circuit

### III. DESIGN PROCEDURES

Turns of reset winding: When the transistor is on, diode D<sub>2</sub>

and D<sub>1</sub> are reverse biased. Diode D<sub>3</sub> is on until V<sub>c2</sub> drops to the reflected input voltage, V<sub>g</sub>\*Nr/Np. During the transistor-on period, V<sub>c2</sub> is approximately equal to the voltage of the clamp winding N<sub>r</sub>.

$$V_{C2} = \frac{N_r}{N_p} \cdot V_g \quad (12)$$

Voltage V<sub>c2</sub> must be greater than the reflected output voltage so that D<sub>1</sub> will not be reverse biased during the transistor-off period, otherwise the energy stored in L<sub>m</sub> will be totally transferred to the capacitor instead of the output winding. Therefore,

$$V_{C2} > \frac{V_o \cdot N_p}{N_s} \quad (13)$$

Substituting (12) into (13), the turns of clamp winding can be determined by the inequality

$$N_r > \frac{V_o \cdot N_p^2}{V_g \cdot N_s} \quad (14)$$

Choice of the clamp capacitance: To meet the requirement of (13), the minimum voltage level of C<sub>2</sub>, V<sub>c min</sub>, in (11) needs to be greater than V<sub>o</sub>\*Np/Ns. Solving the inequality, the capacitance is given as follows

$$C_2 \geq \frac{\frac{I_m^2 \cdot L_{LK}}{4 \cdot V_o^2 \cdot (\frac{N_r}{N_s} \frac{1-D}{D} - \frac{N_p}{N_s})^2}}{(15)}$$

Timing limitation: It is required that during transistor-on time the half cycle of the LC resonant should be completed. This gives a constraint on the maximum value of clamp capacitance.

$$C_2 < \left( \frac{T_{on} N_p}{\pi N_r} \right)^2 \frac{1}{L_{LK}} \quad (16)$$

### IV. SIMULATION AND EXPERIMENTAL RESULTS

PSIM simulation program was used to emulate the performance and a prototype of flyback converter was built as shown in Fig. 7.



Fig. 7. 50W prototype of flyback with energy regenerative snubber

The experiment conditions are:

Input voltage range: 300V ~ 400V  
 Output voltage: 24V  
 Maximum output power: 50W  
 Switching frequency: 100kHz

The figures shown below are in the same time scale. It can be observed from Fig. 8 ~ Fig. 13. that  $t_0 \sim t_1$  is the period when clamp capacitor  $C_2$  discharges through  $Q_1$  and  $N_r$  while  $D_3, C_2$  and  $L_{LK}$  resonant. The current of  $C_2$  is a half sine wave and the voltage of  $C_2$  is a half cosine wave. Between  $t_2$  to  $t_3$ , the snubber is in clamp mode. The energy stored in leakage inductance is transferred to  $C_2$  during this time. The leakage current dropped to zero quickly. In Fig. 9, a gradual drain-to-source voltage-rise is visible when the MOSFET is turned off. Fig. 9, Fig. 11 and Fig. 13 are experimental waveforms which are in accordance with the theoretical analysis and simulation.

For efficiency study, a comparison is made with the traditional RCD method and the LC lossless snubber method. The power efficiencies were measured on the same flyback prototype with different snubbers. The designed parameters of RCD, non-dissipative LC and energy regenerative snubber are given in Table II, Table III and Table IV, respectively. The curves of efficiency of three different snubbers under the same voltage stress are shown in Fig.13. It is observed that the overall efficiency of energy regenerative snubber is about 8% higher than that of RCD and about 2 % higher than that of the non-dissipative LC snubber,

Table II The parameters of flyback with RCD snubber

Np	Ns	$L_m$	$L_{LK}$	$R_{snubber}$	$C_{snubber}$
74	11	2.33mH	36.3uH	20kohm	100nF

Table III The parameters of flyback with Non-dissipative LC snubber

Np	Ns	$L_m$	$L_{LK}$	$L_{snubber}$	$C_{snubber}$
74	11	2.33mH	36.3uH	4.5uH	1nF

Table IV The parameters of flyback with energy regenerative snubber

Np	Ns	$N_r$	$L_m$	$L_{LK}$	$C_{snubber}$
74	11	48	2.33mH	36.3uH	10nF

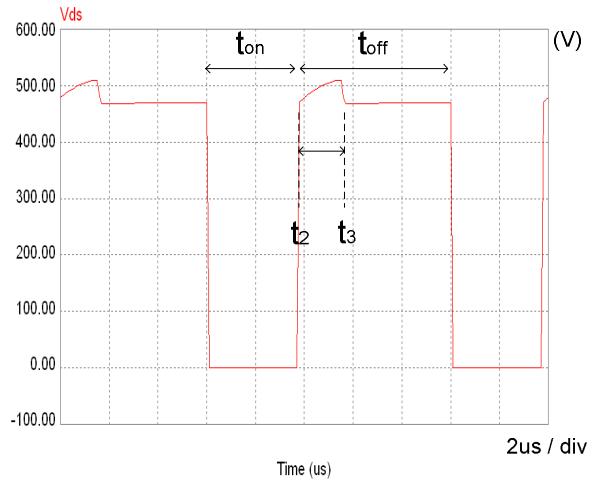


Fig. 8. Simulated voltage waveform of transistor

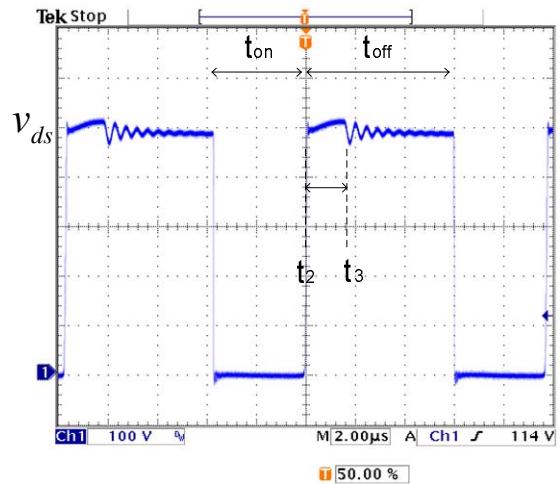


Fig. 9. Experimental voltage waveform of transistor

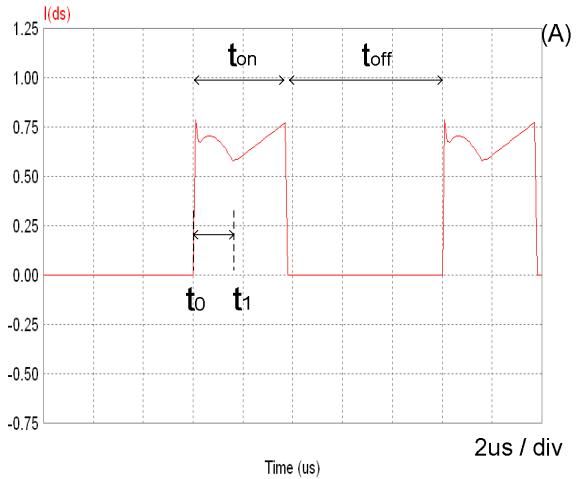


Fig. 10. Simulated current waveform of transistor

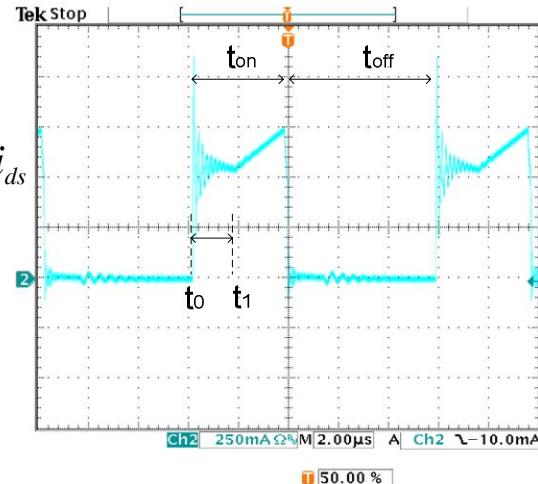


Fig. 11. Experimental current waveform of transistor

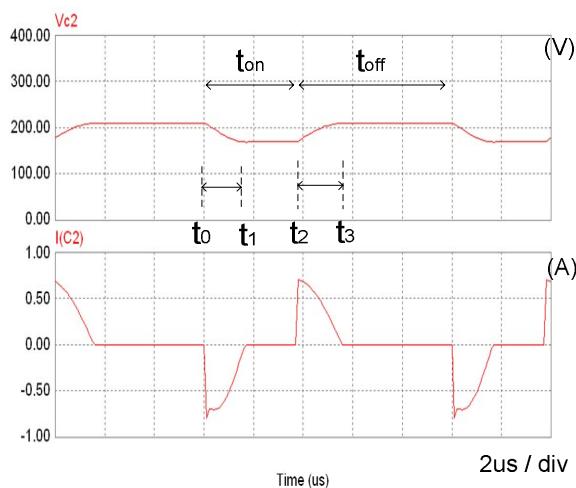


Fig. 12. Simulated voltage and current waveforms of  $C_2$

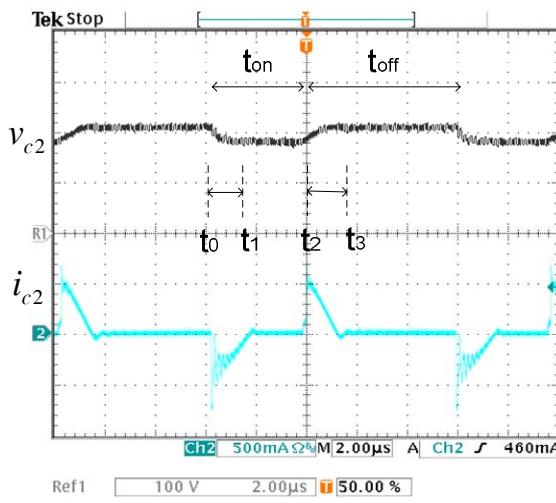


Fig. 13. Experimental voltage and current waveforms of  $C_2$

## V. CONCLUSION

With an RCD snubber, the voltage stress of the switch and the power dissipation of the snubber are a trade-off. They are determined by the value of snubber resistor. The high power dissipation has long been its drawback. The non-dissipative LC snubber can significantly reduce the loss of snubber circuit. However, an extra inductor for the snubber increases the cost and makes design more complicated. In comparison, the voltage stress of the energy regenerative snubber is set by the turns of reset winding  $N_r$  without sacrificing efficiency. Moreover, the clamp winding shares the same core with the transformer, which is cost effective and easier to design. The experimental efficiency in Fig. 14. shows that under the same voltage stress the efficiency of energy regenerative snubber has 8% improvement in average over RCD snubber and 2% improvement over nondissipative LC snubber.

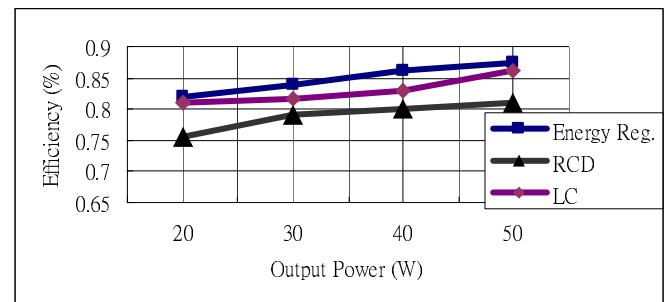


Fig. 14. Experimental efficiency measured with RCD, non-dissipative snubber and energy regenerative snubber.

## REFERENCES

- [1] Moshe Domb, Richard Redl, and Nathan O Sokal "Non-dissipative Turn Off Snubber Alleviates Switching Power Dissipation, Second-Breakdown Stress and VCE Overshoot: Analysis, Design Procedure and Experimental Verification".
- [2] Moshe Domb, Richard Redl, and Nathan O Sokal "Non-dissipative Turn-Off Snubber in a Forward Converter: Analysis, Design Procedure, and Experimental Verification" PCI Proceeding 1985.
- [3] K. M. Smith, Chuanwen Ji, and K. M. Smedley, "Energy regenerative clamp for flyback Converter", UCI, invention disclosure, Sept. 1998.
- [4] Chuanwen Ji, K. Mark Smith, Jr., and Keyue M. Smedley "Cross Regulation in Flyback Converters: Analytic Model and Solution" *IEEE Trans. On Power Electronics*, Vol. 16, No.2, March 2001.
- [5] Alenka Hren, Jozef Korelic, and Miro Milanovic "RC-RCD Clamp Circuit for Ringing Losses Reduction in a Flyback Converter" *IEEE Trans. On Circuits and systems—II:Express Briefs*. Vol. 53. No. 5 May 2006.
- [6] Tsu-Hua Ai, "A Novel Integrated Non-dissipative Snubber for Flyback Converter"
- [7] Robert W. Ericson, and Dragon Maksimovic, "Fundamentals of Power Electronics" Second Edition.
- [8] N. Mohan, T. M. Undeland, and W. P. Robbins, "Power Electronics; Converter, Applications and Design" Third Edition.
- [9] "Snubber Circuits Suppress Voltage Transient Spikes in Multiple Output DC-DC Flyback Converter Power Supplies", Application note 848, [http://www.maxim-ic.com/appnotes.cfm/appnote\\_number/848](http://www.maxim-ic.com/appnotes.cfm/appnote_number/848)